



American Microsemiconductor, Inc.

133 Kings Road Madison, NJ 07940
 Tel: (973) 377-9566 Fax: (973) 377-3078
 email: info@americanmicrosemi.com

Features

- Low Leakage Current
- Flat Junction Capacitance
- High Mechanical Strength

1N34A
Germanium Diode
65 Volt

DO-7

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	---	300	---	7.62	
B	---	107	---	2.72	∅
C	.018	.022	0.46	0.56	∅
D	1.000	---	25.40	---	

Electrical Characteristics @ 25°C Unless Otherwise Specified

Peak Inverse Voltage	PIV	65V	$I_R=1.0\text{mA}$
Average Rectified Current	I_O	50mA	
Peak Forward Surge Current	I_{FSM}	500mA	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F	1.00V	$I_{FM} = 5.0\text{mA};$ $T_J = 25^\circ\text{C}^*$
Maximum Reverse Current	I_R	30uA 500uA	$T_A = 25^\circ\text{C}$ $V_R=10\text{V}$ $V_R=50\text{V}$
Typical Junction Capacitance	C_J	0.8pF	Measured at 1.0MHz, $V_R=0\text{V}$

*Pulse test: Pulse width 300 usec, Duty cycle 2%